

EXHIBIT 1

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Siliconix incorporated

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Attorneys for Defendant
Alpha and Omega Semiconductor Incorporated
and Alpha And Omega Semiconductor Limited

UNITED STATES DISTRICT COURT
NORTHERN DISTRICT OF CALIFORNIA
SAN FRANCISCO DIVISION

SILICONIX INCORPORATED,
a Delaware corporation,

Plaintiff,

v.

ALPHA AND OMEGA
SEMICONDUCTOR INCORPORATED,
a California corporation, and ALPHA AND
OMEGA SEMICONDUCTOR LIMITED,
a Bermuda corporation,

Defendants.

CASE NO. C 03-4803 WHA

STIPULATED PROTECTIVE ORDER

STIPULATION

Pursuant to Federal Rule of Civil Procedure 26, and it appearing that discovery in the above-entitled action will involve the disclosure of confidential information, it is hereby stipulated by and between the Parties through their respective counsel and ordered that the following Protective Order be entered to give effect to the terms and conditions set forth below.

1.0 Definitions

1.1 "Siliconix" means Siliconix incorporated.

1.2 "AOS" means Alpha and Omega Semiconductor Incorporated and Alpha and Omega Semiconductor Limited.

1.3 "Designating Party" means Siliconix or AOS or any non-party producing documents or information under this Protective Order.

1.4 "Receiving Party" means Siliconix or AOS.

1.5 "Protected Information" includes the following categories of information, and shall include documents produced during discovery, answers to interrogatories, responses to requests for admission, depositions, hearing or trial transcripts, and tangible things, the information contained therein and all copies, abstracts, excerpts, analyses or other writings that contain, reflect or disclose such information whether contained in attorney work product or not.

1.5.1 "Confidential" designates Protected Information that a Designating Party believes to be of a proprietary business or technical nature and not readily available to competitors, potential competitors, and/or other third parties.

1.5.2 "Confidential – Attorneys' Eyes Only" designates Protected Information that the Designating Party reasonably believes is "Confidential" information within the meaning of Section 1.5.1, the disclosure of which is likely to cause harm to the competitive position of the Designating Party. Such information may fall into one or more of the following categories:

1.5.2.1 Future Business Plans

1.5.2.2 Current Business Plans

1.5.2.3 New Product Development

- 1 1.5.2.4 New Business Development (for old products)
- 2 1.5.2.5 Trade Secrets (as defined by California law)
- 3 1.5.2.6 Proprietary Engineering Information (not generally
- 4 available to the public)
- 5 1.5.2.7 Computer Source Code or Product Designs
- 6 1.5.2.7 Competitor Market Analysis
- 7 1.5.2.8 Customer Lists
- 8 1.5.2.9 Internal Financial/Accounting Information
- 9 1.5.2.10 Operations Information
- 10 1.5.2.11 Distributor Agreements
- 11 1.5.2.12 License Agreements
- 12 1.5.2.13 Foundry Agreements
- 13 1.5.2.14 Development Agreements
- 14 1.5.2.15 Agreements with Sales Representatives
- 15 1.5.2.16 Prices Charged to Distributors and/or Customers
- 16 1.5.2.17 Business Relationships with Third Parties
- 17 1.5.2.18 Current Product Development and Production
- 18 1.5.2.19 Costs Related Information
- 19 1.5.3 Protected Information shall not include: information that is in the
- 20 public domain at the time of disclosure (except such information in the public domain which may
- 21 be treated as a trade secret due to the effort involved in collecting and maintaining such
- 22 information); information which after disclosure is published or becomes part of the public
- 23 domain through no fault of a Party receiving information under this Protective Order, but only
- 24 after it is published or comes into the public domain (subject to the same trade secret exclusion
- 25 stated above); information that is in the possession of a Party receiving such information without
- 26 any confidentiality obligations at the time of disclosure; information independently derived by a
- 27 Party receiving Protected Information without reference to any Protected Information, as
- 28

1 evidenced by documentation; or information disclosed by a third party having the legal right to do
2 so.

3 1.6 "Document" shall have the meaning ascribed to it in Federal Rule of Civil
4 Procedure Rule 34(a).

5 1.7 "Employees" means regular full or part-time employees and also temporary
6 personnel who are providing secretarial, clerical and/or administrative services only of the
7 designated employer.

8 2.0 Designations of Protected Information

9 2.1 Each Designating Party who produces or discloses any material that the
10 Designating Party reasonably believes to contain or reveal Protected Information may designate
11 the same Confidential, or Confidential – Attorneys' Eyes Only.

12 2.2 Documents may be designated as Confidential only if, prior to production,
13 the document is clearly marked with a legend which states:

14 CONFIDENTIAL

15 2.3 Documents may be designated as Confidential – Attorneys' Eyes Only
16 only if, prior to production, the document is clearly marked with a legend which states:

17 CONFIDENTIAL – ATTORNEYS' EYES ONLY

18 2.4 An answer to an Interrogatory or Request for Admission may be designated
19 as the appropriate category of Protected Information by a statement made therein.

20 2.5 A deposition transcript or a portion thereof may be designated as the
21 appropriate category of Protected Information by so designating on the record at the deposition or
22 designating any portion of the transcript as "Confidential" or "Confidential – Attorneys' Eyes
23 Only" within thirty (30) days following the mailing of the transcript or videotape by the court
24 reporter or videographer. Such notice thereof shall be made in writing to the reporter, with copies
25 to all other counsel, designating the portions of the transcript or videotape that contain Protected
26 Information as either Confidential or Confidential – Attorneys' Eyes Only, and directing the
27 reporter to mark that portion of the transcript or videotape accordingly. Until expiration of the
28

1 thirty day period specified in this Section 2.5, all deposition transcripts and/or videotapes shall be
2 considered and treated as Confidential – Attorneys’ Eyes Only.

3 2.6 Counsel of record shall exert their best efforts to raise claims of
4 confidentiality prior to the disclosure of Protected Information.

5 2.7 Notwithstanding the provisions of Sections 2.2 – 2.6 of this Protective
6 Order, failure of counsel to designate and/or mark any Protected Information as “Confidential” or
7 “Confidential – Attorneys’ Eyes Only” as provided above shall not preclude the disclosing Party
8 from thereafter in good faith making such a designation and requesting the Receiving Party to so
9 mark and treat such Protected Information so designated. After such designation, such Protected
10 Information shall be fully subject to this Protective Order and treated thereafter according to the
11 new or corrected designation subject to any objection procedure provided herein. The Receiving
12 Party, however, shall incur no liability for disclosures made prior to notice of such designation.
13 The Parties shall confer in good faith to correct the designation and shall take all necessary steps
14 to prevent further dissemination of the subject materials.

15 3.0 Disclosure of Protected Information

16 3.1 Information designated “Confidential” may only be disclosed to the
17 following persons:

18 3.1.1 outside counsel of record for Siliconix or AOS in this Action and
19 the Employees of outside counsel of record (“Outside Counsel”) who are assisting in this
20 litigation and whose duties require access to Protected Information;

21 3.1.2 independent experts and/or consultants retained by counsel of
22 record for Siliconix or AOS, subject to the provisions of Section 4.0 of this Protective Order;

23 3.1.3 in-house attorneys for each Party, and Employees who are assisting
24 such in-house attorneys in this litigation in filing and/or administrative duties and whose duties
25 require access to Protected Information;

26 3.1.4 Employees or representatives of each Party who are necessary to
27 the Party’s preparation and pursuit of claims and defenses in this action;
28

1 3.1.5 third parties specifically retained to assist outside counsel in
2 copying or computer coding of documents, but only for purposes of copying or computer coding
3 Protected Information;

4 3.1.6 qualified persons taking or recording testimony involving Protected
5 Information and their Employees whose duties require access to Protected Information; and

6 3.1.7 the Court and the Court's staff; and

7 3.1.8 such other persons as the Parties agree to in writing prior to any
8 disclosure of Protected Information.

9 3.2 Information designated Confidential – Attorneys' Eyes Only, including
10 copies thereof, extracts therefrom, compilations and/or summaries thereof and any information
11 therein, may only be disclosed to the following persons: persons falling within the categories
12 specified in Sections 3.1.1, 3.1.2, 3.1.5, 3.1.6, and 3.1.7 of this Protective Order, but shall in no
13 case be disclosed to persons who are involved in competitive decision making or intellectual
14 property licensing decisions for Siliconix or AOS, or to persons who are currently prosecuting,
15 supervising, advising or assisting in any way in the preparation and/or prosecution of any new or
16 pending patent application, continuation, divisional, renewal, substitute or convention application
17 relating to field-effect transistors ("FETs"), or any portion thereof, whether design or utility,
18 whether in the United States or abroad (including applications filed under the Patent Cooperation
19 Treaty), whether or not claiming priority from the patents asserted in this litigation or any foreign
20 counterpart thereof, on behalf of themselves, their employer, any Party to this litigation or any
21 third party (hereafter "Prosecution Counsel" or "Prosecution Consultant"), and further provided
22 that such persons shall not during the pendency of, and for a period of one year following the
23 conclusion of this action (including any appeals), engage in any such prosecution, supervision,
24 advice or assistance in any way in the preparation and/or prosecution of any new patents or patent
25 applications, including provisional patent applications relating to FETs.

26 3.3 Protected Information shall not be made available to any person except as
27 authorized under this Protective Order, and no person identified in Sections 3.1.2, and 3.1.5 shall
28 have access to Protected Information without having first read, acknowledged and agreed in

1 writing (in the form of the Declaration for Protective Order attached hereto as Exhibit A) to be
2 bound by this Protective Order. A file of all such written acknowledgments shall be maintained
3 by the Party obtaining them, and copies of such written acknowledgments shall be provided to all
4 counsel of record upon request at the conclusion of this action or if circumstances arise which
5 create reasonable concern over the adherence to this Protective Order.

6 3.4 Each individual who receives any materials designated as "Confidential" or
7 "Confidential – Attorney's Eyes Only" hereby agrees to subject himself or herself to the
8 jurisdiction of this Court for purposes of any proceedings relating to the performance under,
9 compliance with or violation of this Protective Order.

10 3.5 If the recipient of any Protected Information learns that, by inadvertence or
11 otherwise, it has disclosed Protected Information to any person or in any circumstance not
12 authorized under this Protective Order, the Receiving Party must immediately (a) notify in
13 writing the Designating Party of the unauthorized disclosures, (b) use its best efforts to retrieve all
14 copies of the Protected Information, (c) inform the person or persons to whom unauthorized
15 disclosures were made of all the terms of this Order, and (d) request such person or persons to
16 execute the declaration and undertaking in the form attached hereto as Exhibit A.

17 4.0 Objections to Disclosures

18 4.1 Not less than ten (10) days prior to the initial disclosure of Protected
19 Information to any person falling under the provisions of Sections 3.1.2 of this Protective Order,
20 the Party planning to make such disclosure shall serve (by facsimile and mail) the name, address,
21 present employer, title, resume, and a signed Declaration in the form of Exhibit A of the proposed
22 recipient on the Designating Party (and to the opposing Party, if the Designating Party is other
23 than Siliconix or AOS).

24 4.2 Within the ten (10) day period before disclosure of the Protected
25 Information to the proposed recipient, the Party or non-Party whose Protected Information is
26 concerned may serve (by facsimile and mail) a written objection to disclosure to such person.
27 Such an objection shall stay disclosure to the proposed recipient. Failure to serve a written notice
28 of objection within ten (10) days shall be deemed approval of a proposed recipient.

1 4.3 If a written objection is served pursuant to Section 4.2, the Parties shall
2 attempt to resolve the objection by meeting and conferring within ten (10) days of service of the
3 written objection. If the objection is not resolved by meeting and conferring, the Party seeking to
4 prevent disclosure shall file a motion, to be heard on the earliest date available. Failure to file
5 such a motion within ten (10) days of meeting and conferring or at the conclusion of the ten-day
6 period to meet and confer shall preclude a Party from objecting to the disclosure of Protected
7 Information to the person to whom the objection is directed. The disclosure of Protected
8 Information to such proposed person shall be withheld pending the ruling of the Court on any
9 such motion. On any such motion, the Party seeking to prevent disclosure to a person proposed
10 for approval shall have the burden of proof.

11 4.4 If at any time during the pendency or trial of this Action, counsel for any
12 Party claims that a Designating Party is unreasonably designating certain information as
13 Confidential or Confidential – Attorneys’ Eyes Only, the objecting Party may serve a captioned
14 notice of objection on the Designating Party and all Parties, identifying with particularity the
15 items to which the designation is challenged, stating the basis for each challenge, and proposing a
16 new designation for each item. If the Designating Party does not re-designate the material within
17 ten (10) days after service of such notice, the objecting Party may file and serve a motion for an
18 order that the material be re-designated. On any such motion, the Party seeking to prevent
19 re-designation shall have the burden of proof. The original designation shall remain effective
20 until three (3) business days after an Order is entered re-designating the materials. The Court
21 may award sanctions on any motion concerning the challenge of a designation if the Court finds
22 that any Designating Party’s or Receiving Party’s position was taken without reasonable
23 justification.

24 5.0 Use of Protected Information

25 5.1 Protected Information disclosed pursuant to this Protective Order shall,
26 unless otherwise ordered by this Court, be used by a recipient thereof solely for the purpose of
27 this Action and not for any other action or for any business or competitive purposes or for any
28 other reason. Protected Information shall not be used for any purposes other than in the

1 prosecution or defense of claims asserted in this Action. In no event shall any person receiving
2 Protected Information use it for commercial or competitive purposes, including any use in the
3 preparation and/or prosecution of any new or pending patent application, continuation, divisional,
4 renewal, substitute or convention application, or any portion thereof, whether design or utility,
5 whether in the United States or abroad (including applications filed under the Patent Cooperation
6 Treaty), or make any public disclosure of the contents thereof. Nothing contained in this
7 Protective Order, however, shall affect the right of the Designating Party to disclose information
8 designated solely by it under this Protective Order.

9 5.2 No person shall disclose to anyone not specified in Section 3.0 of this
10 Protective Order any Protected Information without prior written consent of the Designating Party
11 or further Order of this Court.

12 6.0 Depositions Involving Protected Information

13 6.1 At any deposition session, when counsel of record for a Party deems that a
14 question and/or the answer to a question will result in the disclosure of Protected Information,
15 counsel may designate as Confidential or Confidential – Attorneys’ Eyes Only the portion of the
16 transcript or videotape containing such question or answer.

17 6.2 Any portion of a transcript designated as Confidential or Confidential –
18 Attorneys’ Eyes Only Protected Information shall be transcribed separately from the remainder of
19 the transcript of the deposition and designated in the manner set forth in Section 2.0 of this
20 Protective Order.

21 6.3 During the portion of a deposition in which Protected Information will be
22 disclosed, counsel of record for the Designating Party may request that all persons other than the
23 individuals specified in Section 3.1 (for Confidential Protected Information) or Section 3.2 (for
24 Confidential – Attorneys’ Eyes Only Protected Information) leave the deposition room prior to
25 disclosure of Protected Information. The failure of such other persons to comply with a request
26 of this type shall constitute substantial justification for counsel of record to advise the witness not
27 to answer the question.
28

1 6.4 Where appropriate, in light of the amount of Protected Information likely
2 to be disclosed at a given deposition, counsel of record for Siliconix and counsel of record for
3 AOS may agree at the beginning of the deposition that the entire transcript and/or videotape shall
4 be designated Confidential or Confidential – Attorneys’ Eyes Only subject to review of the
5 transcript and withdrawal of any unnecessary Confidential or Confidential – Attorneys’ Eyes
6 Only designation by the Designating Party within thirty (30) days of receipt of the transcript.
7 Section 6.4 is made expressly subject to the provisions set forth in Section 4.4.

8 6.5 A person not otherwise permitted to receive a disclosure of Protected
9 Information under Section 3.1 of this Protective Order may be shown such Protected Information
10 and may be examined or deposed about such Protected Information if the Protected Information
11 itself reveals that such person legitimately had access to that Protected Information at some
12 earlier time. This exception does not permit any person who has received a disclosure of
13 Protected Information to have access to any other Protected Information, even if that information
14 is similar or of the same type.

15 7.0 Court Filings Including Protected Information

16 7.1 Any written material constituting, containing or disclosing Protected
17 Information that is lodged or filed with the Clerk of the Court, including Court papers, shall be
18 submitted in compliance with Civil Local Rule 79-5 and marked “FILED UNDER SEAL,” and
19 endorsed on the front page of the written material itself with a statement substantially in the
20 following form:

21 CONFIDENTIAL
22 SUBJECT TO PROTECTIVE ORDER
23 IN CIVIL ACTION NO. C 03-4803 WHA
24 UNITED STATES DISTRICT COURT FOR THE
25 NORTHERN DISTRICT OF CALIFORNIA – SAN FRANCISCO DIVISION

26 or

27 CONFIDENTIAL – ATTORNEYS’ EYES ONLY
28 SUBJECT TO PROTECTIVE ORDER
29 IN CIVIL ACTION NO. C 03-4803 WHA
30 UNITED STATES DISTRICT COURT FOR THE
31 NORTHERN DISTRICT OF CALIFORNIA – SAN FRANCISCO DIVISION

1 7.2 All such materials shall be accepted by the Clerk of the Court for filing and
2 shall be maintained by the Clerk of the Court separate from the public records in this action and
3 shall be released only upon further Order of the Court.

4 7.3 All documents, exhibits or papers filed in connection with any proceedings
5 related to compliance with, performance under, construction of or violation of this Protective
6 Order, shall be filed under seal pursuant to Civil Local Rule 79-5.

7 8.0 Pretrial and Trial

8 8.1 This Protective Order is intended to regulate the handling of Protected
9 Information during the pretrial period of this litigation, but shall remain in force and effect
10 thereafter until modified, superseded or terminated on the record by agreement of the Parties
11 hereto or by Order of this Court.

12 8.2 Subject to the Federal Rules of Evidence, Protected Information may be
13 offered in evidence at trial or any Court hearing in this Action, provided that:

14 8.2.1 the proponent of the evidence advises the Court and the
15 Designating Party that Protected Information will be offered prior to its offer and the Designating
16 Party has appropriate opportunity to object to the disclosure of the Protected Information;

17 8.2.2 any documents, exhibits or papers containing Protected Information
18 shall be filed under seal pursuant to Civil Local Rule 79-5;

19 8.2.3 the evidence be received *in camera* or under other conditions to
20 prevent disclosure to any persons other than the judge, the jury, the court reporter, counsel of
21 record, any witness testifying with respect to the evidence, and other persons who are entitled to
22 receive the appropriate category of Protected Information under the terms of this Protective
23 Order, and

24 8.2.4 the trial or Court hearing transcript is treated in the manner
25 specified in Section 6.0 of this Protective Order.

26 9.0 General Provisions

27 9.1 Upon final termination of this Action with respect to any Party, that Party
28 shall, at the option of the Designating Party, either return to the Designating Party or destroy all

1 Protected Information in its possession, except such pretrial and trial records as are regularly
2 maintained by outside counsel in the ordinary course of business, which records must be
3 protected in conformity with this Protective Order. The termination of proceedings in this Action
4 shall not thereafter relieve the Parties from the obligation to maintain the confidentiality of all
5 Protected Information received pursuant to this Protective Order, including the provisions relating
6 to prosecution of patents set forth in paragraphs 3.2 and 5.1.

7 9.2 This Protective Order is intended to provide a mechanism for the handling
8 of Protected Information, the disclosure or production of which is objected to only on the basis of
9 Confidentiality. Each Party reserves the right to object to any disclosure of information or
10 production of any document it deems Protected Information on any other ground it may deem
11 appropriate. The designation of Protected Information pursuant to this Protective Order shall not
12 create any presumption with respect to the Confidential, proprietary, or trade secret nature of any
13 information, documents or things.

14 9.3 The Parties may, by joint stipulation, apply to amend this Protective Order.
15 The amendment shall take effect once the stipulation is entered by the court.

16 9.4 The Court retains jurisdiction to amend this Protective Order without
17 agreement of the Parties and to issue Orders concerning Protected Information disclosed under
18 this Protective Order.

19 9.5 Notwithstanding the foregoing provisions, counsel for either Party may
20 give advice and opinions to his or her client based on his or her evaluation of information
21 disclosed by the opposing Party or a third party and designated as Confidential or Confidential –
22 Attorneys' Eyes Only, including for purposes of settlement discussions.

23 9.6 Nothing in this Protective Order shall limit or restrict the manner in which
24 the Parties shall handle their own Protected Information.

25 9.7 Adherence to this Protective Order in no way constitutes an admission by
26 any Party that any information provided in this Action and not subject to this Protective Order is
27 not proprietary or confidential.
28

1 9.8 This Protective Order shall not abrogate or diminish any contractual,
2 statutory or other legal obligation or right of any Party or person, nor obligate any Party or person
3 to provide any discovery to which it asserts objections.

4 9.9 Nothing in the foregoing provisions of this Protective Order shall be
5 deemed to preclude any Party from seeking and obtaining, on an appropriate showing, such
6 additional protection with respect to the confidentiality of these proceedings or specific
7 documents or testimony as that Party may deem appropriate, including but not limited to
8 restrictions on public disclosure or disclosure to competitors.

9 9.10 The terms of this Protective Order shall apply to confidential documents or
10 material produced or disclosed by third parties in connection with this action if such third party
11 wishes to designate the document or information Protected Information.

12 9.11 Each Party reserves the right to apply to the Court to modify the terms of
13 this Protective Order in the event that the Party believes that it is necessary. In the event such an
14 application is made, all persons described herein shall be bound by this Protective Order until it is
15 modified by the Court.

16 9.12 The disclosure of Protected Information to any attorney of record shall not
17 prevent or disqualify that attorney of record from representing any Party or any non-party in any
18 future litigation.

19 9.13 If any Party or non-party, having received Protected Information, receives
20 a subpoena or other compulsory process from any other person or entity seeking the production of
21 the Protected Information produced by the Designating Party, counsel for the Designating Party
22 shall be notified in writing immediately and in no event more than three (3) court days after the
23 receipt of the subpoena or other compulsory process and such notification shall include copies of
24 the subpoena or compulsory process. Absent the consent of the Designating Party, the Party or
25 person receiving such subpoena or compulsory process shall refrain to the fullest extent
26 permissible under law from producing the subpoenaed Protected Information. The Party or
27 person receiving such subpoena or compulsory process also must immediately inform in writing
28 the party who caused the subpoena or Order to issue in the other litigation that some or all the

1 material covered by the subpoena or Order is the subject of this Protective Order. In addition, the
2 Receiving Party must deliver a copy of this Protective Order promptly to the Party in the other
3 action that caused the subpoena or Order to issue. The purpose of imposing these duties is to alert
4 the interested Parties to the existence of this Protective Order and to afford the Designating Party
5 in this Action an opportunity to try to protect its confidentiality interests in the court from which
6 the subpoena or Order issued. The Designating Party shall bear the full burden and all expenses
7 of seeking protection in that court of its Protected Information, and nothing in these provisions
8 should be construed as authorizing or encouraging a Party to this Action to disobey a lawful
9 directive from another court.

10
11 Dated: May 4, 2004

QUINN EMANUEL URQUHART
OLIVER & HEDGES

12
13 By: /s/ Daniel N. Kassabian

14 Daniel N. Kassabian
15 Attorneys for Plaintiff
Siliconix incorporated

16 Dated: May 4, 2004

ORRICK, HERRINGTON & SUTCLIFFE LLP

17
18 By: /s/ Stephen N. Adams

19 Stephen N. Adams
20 Attorneys for Defendants
Alpha and Omega Semiconductor Incorporated
21 and Alpha and Omega Semiconductor Limited
22
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EXHIBIT A

UNITED STATES DISTRICT COURT
NORTHERN DISTRICT OF CALIFORNIA
SAN FRANCISCO DIVISION

SILICONIX INCORPORATED,
a Delaware corporation,

Plaintiff,

v.

ALPHA AND OMEGA
SEMICONDUCTOR INCORPORATED,
a California corporation, and ALPHA AND
OMEGA SEMICONDUCTOR LIMITED,
a Bermuda corporation,

Defendants.

Case No. C 03-4803 WHA

**DECLARATION AND UNDERTAKING
OF _____**

I, _____, being duly sworn, state that:

1. My address is _____.

2. My present employer is _____.

3. My present occupation or job description is _____.

4. I have received a copy of the Stipulated Protective Order entered in the
above-captioned action signed by the Honorable William Alsup on _____, 2004.

5. I have carefully read and understand the provisions of the Stipulated Protective
Order.

6. I will comply with and agree to be bound by all of the provisions of the Stipulated
Protective Order.

7. I will hold in confidence, will not disclose to anyone not qualified under the
Stipulated Protective Order, and will use only for purposes of the above-captioned action, any

1 “Confidential,” and or “Confidential – Attorneys’ Eyes Only” or which is disclosed to me.

2 8. I will return all “Confidential” and “Confidential Attorneys’ Eyes Only” which
3 comes into my possession, and documents or things which I have prepared relating thereto, to
4 counsel for the Party by whom I am retained.

5 9. I understand and acknowledge that violation of this Undertaking or the Stipulated
6 Protective Order may be punishable by Contempt of Court. I hereby submit to the jurisdiction of
7 this Court for the purpose of enforcement of the Stipulated Protective Order in the
8 above-captioned action.

9 I declare under penalty of perjury under the laws of the United States of America that the
10 foregoing is true and correct.

11 Executed this _____ day of _____, 200__ in _____.

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EXHIBIT 2

Morgan, Lewis & Bockius LLP
2 Palo Alto Square
3000 El Camino Real, Suite 700
Palo Alto, CA 94306
Tel: 650.843.4000
Fax: 650.843.4001
www.morganlewis.com

Morgan Lewis
C O U N S E L O R S A T L A W

Harry F. Doscher
Associate
650.843.7565
hdoscher@morganlewis.com

October 23, 2007

VIA Email and First Class Mail

Matthew R. Hulse, Esq.
Townsend and Townsend and Crew LLP
Two Embarcadero Center, 8th Floor
San Francisco, CA 94111
mrhulse@townsend.com

Re: *Alpha & Omega Semiconductor, Ltd. and Alpha & Omega Semiconductor, Inc. v. Fairchild Semiconductor Corporation,*
Nos. C 07-2638 JSW and C 07-2664 JSW (N.D. Cal.)

Dear Matthew:

AOS has retained Dr. C. Andre T. Salama as a consultant in this action. This letter serves as notice of our intent to disclose to Dr. Salama information designated as "Confidential" or "Highly Confidential – Attorneys' Eyes Only" under the Protective Order. Please find attached Dr. Salama's C.V. as well as his executed agreement to be bound by the terms of the Protective Order.

Dr. Salama has provided consulting services to the following entities within the past five years:

- Nortel Networks Inc., from 2002-2004
- Gennum Corporation, from 2002-2004
- Semiconductor Insights Inc., from 2005-2006
- PMC Sierra Inc., from 2002-2004
- Zarlink Inc., from 2002-2004
- Lucent Technologies Inc., from 2004-2005
- Siemens Inc., in 2006

Within the last five years, Dr. Salama has provided professional services in connection with the following litigations:

Matthew R. Hulse, Esq.
October 23, 2007
Page 2

Morgan Lewis
C O U N S E L O R S A T L A W

- *Matsushita Electric Industrial Company, LTD v. Siliconix Incorporated*, 3:06-cv-01953-WHA, filed 03/15/2006 in the Northern District of California, San Francisco Division (retained by Matsushita)
- *Alpha & Omega Semiconductor, Inc. v. Siliconix, Inc.*, Reference Co. 1110009946, filed February 28, 2007 with the JAMS Resolution Center, San Jose, California (retained by AOS)

Please let me know within the schedule prescribed by the Protective Order if you have any objection regarding Dr. Salama.

Best Regards,



Harry F. Doscher

Enclosures

cc: Leonard J. Augustine, Jr., Esq. (w/Enclosures via email: ljaugustine@townsend.com)
Eric P. Jacobs, Esq. (w/Enclosures via email: epjacobs@townsend.com)
Igor Shoiket (w/Enclosures via email: ishoiket@townsend.com)
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CURRICULUM VITAE

C. ANDRE T. SALAMA

October 2007

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• SHORT FORM

C. ANDRE T. SALAMA received the B.A.Sc. (Hons.) M.A.Sc. and Ph. D. degrees, all in Electrical Engineering, from the University of British Columbia in 1961, 1962 and 1966 respectively.

From 1962 to 1963 he served as a Research Assistant at the University of California, Berkeley. From 1966 to 1967 he was employed at Bell Northern Research, Ottawa, as a Member of Scientific Staff working in the area of integrated circuit design. Since 1967 he has been on the staff of the Department of Electrical and Computer Engineering, University of Toronto where he holds the J.M. Ham Chair in Microelectronics. In 1992, he was appointed University Professor (presently Emeritus) for scholarly achievements and preeminence in the field of microelectronics. In 1989-90, he was awarded the ITAC/NSERC Research Fellowship in information technology. In 1994, he was awarded the Canada Council I.W. Killam Memorial Prize in Engineering for outstanding career contributions to the field of microelectronics. In 2000, he received the IEEE Millenium Medal. In 2003, he received the Outstanding Lifetime Achievement Award from the Canadian Semiconductor Technology Conference for seminal and outstanding contributions to semiconductor device research and promotion of Canadian University research in microelectronics. He received the NSERC Lifetime Achievement Award of Research Excellence for outstanding and sustained contributions to the field of microelectronics (2004), the Networks of Centres of Excellence (NCE) Recognition Award for research excellence and outstanding leadership (2004) and the ITAC Outstanding Service Award for contributions to Microelectronics in Canada (2006).

He was associate editor of the IEEE Transactions on Circuits and Systems in 1986-88 and a member of the International Electron Devices Meeting (IEDM) Technical Program Committee in 1980-82, 1987-89 and 1996-98. He was the chair of the Solid State Devices Subcommittee for IEDM in 1998 and was a member of the editorial board of Solid State Electronics from 1984 to 2002. He is presently a member of the editorial board of the Analog IC and Signal Processing Journal and the Technical Program Committee of the International Symposium on Power Semiconductor Devices and ICs (ISPSD) and the Technical Program Committee of the International Symposium on Low Power Electronics and Design (ISLPED). He chaired the technical program committee of ISPSD in 1996 and was the general chair for the conference in 1999.

Dr. Salama is the Scientific Director of Micronet, a network of centres of excellence focussing on microelectronics research and funded by the Canadian Government and Industry.

He has published extensively in technical journals, is the holder of eleven patents and has served as a consultant to the semiconductor industry in Canada and the U.S. His research interests include the design and fabrication of semiconductor devices and integrated circuits with emphasis on deep submicron devices as well as circuits and systems for high speed, low power signal processing applications.

Dr. Salama is a Fellow of the Institute of Electrical and Electronics Engineers, a Fellow of the Royal Society of Canada, a Fellow of the Canadian Academy of Engineering, a Fellow of the Engineering Institute of Canada, a member of the Association of Professional Engineers of Ontario and the Electrochemical Society.

● GENERAL DATA

DATE OF BIRTH: September 27, 1938

CITIZENSHIP: Canadian

LANGUAGES: French

UNIVERSITY EDUCATION:

University of British Columbia (E.E.) 1964-1966

University of California, Berkeley (E.E.) 1963-1964

University of British Columbia (E.E.) 1957-1962

DEGREES:

Ph.D. (E.E.) 1966, University of B.C.

M.A.Sc. (E.E.) 1962, University of B.C.

B.A.Sc. (E.E.) (Honours) 1961, University of B.C.

THESES:

Ph.D.: Silicon on Sapphire (SOS) Thin Film Transistors
Supervisor: Prof. L. Young

M.A.Sc.: Static and Dynamic Characteristics of Series
Connected Tunnel Diodes and their Applications
in Digital Circuits
Supervisor: Prof. M.P. Beddoes.

PROFESSIONAL ENGINEERING REGISTRATION: Ontario (1970 to present)

SCIENTIFIC AND PROFESSIONAL SOCIETIES:

- **Fellow^{*} - Engineering Institute of Canada (2007 to present)**
- **Fellow^{*} - Canadian Academy of Engineering (2005 to present)**
- **Fellow^{**} - Royal Society of Canada (2001 to present)**
- **Fellow^{***} - Institute of Electrical and Electronics Engineers (IEEE) (1987 to present)**
- Member - Innovation Management Association of Canada (IMAC) (1991 to present)
- Member - Electrochemical Society (1967 to present)
- Chair - IEEE Toronto Section (1985 to 1987)
- Vice Chair - IEEE Toronto Section (1983 to 1985)
- Secretary - IEEE Toronto Section (1981 to 1983)
- Treasurer - IEEE Toronto Section (1979 to 1981)

* In recognition of notable and outstanding contributions to the field of microelectronics.

** For innovation, creativity and leadership in semiconductor device research and integrated circuit design.

*** For contributions to the development of power semiconductor devices and the design of integrated circuits.

AWARDS:

- **ITAC Outstanding Service Award, 2006^{*}**
- **NSERC Lifetime Achievement Award of Research Excellence, 2004⁺**
- **Networks of Centres of Excellence (NCE) Recognition Award, 2004⁺⁺**
- **IEEE Toronto Section Centennial Medal, 2003⁺⁺⁺**
- **Outstanding Lifetime Achievement Award, Canadian Semiconductor Technology Conference, 2003⁺⁺⁺⁺**
- **IEEE Millenium Medal, 2000^{*}**
- **Canada Council I.W. Killam Memorial Prize in Engineering, 1994^{**}**
- **ITAC/NSERC Research Fellowship in Information Technology, 1989-1990.^{***}**
- National Research Council Scholarship, 1965-1966
- National Research Council Scholarship, 1964-1965
- National Research Council Scholarship, 1962
- Northern Electric Graduate Research Fellowship. 1961-1962
- B.C. Electric Scholarship in E.E., 1960-1961
- B.C. Electric Proficiency Scholarship, 1958-1959

LISTED:

- Who's Who in Canada (1994 to present)
- Who's Who in Ontario (1994 to present)
- Who's Who in America (1991 to present)
- Men of Achievement (1990 to present)
- International Leaders in Achievement (1990 to present)
- Dictionary of International Biography (1990 to present)
- Men and Women of Distinction (1990 to present)
- Who's Who in Engineering (1980 to present)
- American Men of Science (1973 to present)
- Who's Who in the East (1973 to present)

PRESENT POSITION:

- **University Professor^{****} (Emeritus)**
Dept. of Electrical and Computer Engineering, University of Toronto, Toronto, Ontario, Canada, M5S 3G4

REFERENCES:

- Dr. A.R. Boothroyd, Professor, Dept. of Electronics. Carleton University, Ottawa, Ontario, Canada K1S 5B6.
- Dr. D. Hodges, Department of Electrical Engineering and Computer Sciences, University of California, Berkeley, California, 94720, U.S.A.
- Dr. L. Young, Professor, Department of Electrical Engineering, University of British Columbia, Vancouver, B.C. Canada V6T 1W5
- Dr. L.T. Bruton, Professor, Department of Electrical Engineering, University of Calgary, Calgary, Alberta, Canada T2N 1N4.
- Dr. H. Pépin, Professor, INRS Energie et Matériaux. C.P. 1020, Varennes, Quebec, Canada J3X 1S2.
- Dr. M. Kuhn, President, Econ Tech. Consulting and Management Services, Research Triangle World Trade Centre, 2525 Meridian Pkwy., Suite 50, P.O. Box 13487, Research Triangle Park, N. Carolina 27709, USA.

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- **For outstanding contributions to Microelectronics in Canada.**
 - + **For outstanding and sustained contributions to the field of microelectronics.**
 - ++ **For research excellence and outstanding leadership.**
 - +++ **In recognition of outstanding professional contributions.**
 - ++++ **For seminal and outstanding contributions to semiconductor device research and promotion of Canadian University research in microelectronics.**
 - * **For contribution to Electrical Engineering research.**
 - ** **In recognition of outstanding achievement and exceptional contribution to the advancement of research in Electrical Engineering.**
 - *** **For contribution to the field of information technology, specifically microelectronics.**
 - **** **Only one percent of active tenured faculty at the University of Toronto are granted this significant honour (about 30 throughout the University).**

- Dr. Gabor C. Temes, Professor, Dept. of Electrical and Computer Engineering, Elec. & Comp. Eng. Bldg., Room 202, Oregon State University, Corvallis, Oregon 97331-3211, USA

• ACADEMIC EXPERIENCE

1. University of Toronto, Department of Electrical Engineering
 Positions: "University Professor" (July 1992 - present)
 J.M. Ham Chair in Microelectronics (July 1987-October 1997)
 Professor (July 1977-June 1992)
 Associate Professor (July 1970-June 1977)
 Assistant Professor (September 1967-July 1970)

 Courses Taught:
 Undergraduate: Electronic Circuits
 Integrated Circuits
 Physical Electronics

 Graduate: VLSI Technology
 Semiconductor Devices
 Bipolar Integrated Circuit Design
 MOS/LSI Design and Applications
 VLSI Systems
 VLSI Design Methodology
2. Catholic University of Leuven, Belgium
 Position: Visiting Professor, July 1975-July 1976
3. University of British Columbia
 Position: Teaching Assistant, September 1964-June 1966
4. University of California, Berkeley
 Position: Teaching Assistant, January 1963-June 1964.

• RESEARCH AND CONSULTING EXPERIENCE

Dr. Salama has been involved in research in the areas of semiconductor devices and integrated circuits and has acted as a consultant to the semiconductor industry in Canada and the USA.

• RESEARCH GRANTS/CONTRACTS

During his career at the University of Toronto, Dr. Salama has been the recipient of over \$60M in research grants and contracts from federal, provincial and industry sources.

● PUBLICATIONS AND PATENTS

I.	Refereed Publications Appearing in Scientific Journals	186
II.	Conference Papers (in refereed conference proceedings)	155
III.	Patents	17
IV.	Papers Appearing in Books	7

I. REFEREED PUBLICATIONS APPEARING IN SCIENTIFIC JOURNALS:

I.(A) FULL JOURNAL PAPERS

- I.Y. Park and C.A.T. Salama, "Super Junction LDMOS Transistors", IEEE Circuits and Devices, vol. 22, pp. 10-15, December 2006.
- F. Mahmoudi and C.A.T. Salama, "8GHz 1V, CMOS Quadrature Downconverter for Wireless Applications", J. on Analog Integrated Circuits and Signal Processing, vol. 48, pp. 185-197, 2006.
- R. Aroca and C.A.T. Salama, "Wide Dynamic Range Parallel Feedback Transimpedance Amplifier for 10 Gb/s Optical Links", J. on Analog Integrated Circuits and Signal Processing, vol. 48, pp. 167-174, 2006.
- I.Y. Park and C.A.T. Salama, "New Super Junction LDMOST with N-Buffer Layer", IEEE Trans. on Electron Devices, vol. 53, pp. 1909-1913, 2006.
- S. Hamed Haghighi and C.A.T. Salama, "CMOS Wireless Phase-Shifted Transmitter", IEEE J. of Solid State Circuits, vol. 39, pp. 1241-1252, 2004.
- S. Nassif-Khalil, L.Z. Hou and C.A.T. Salama, "Super Junction/RESURF LDMOST (SJR-LDMOST)", IEEE Trans. On Electron Devices, vol. 51, pp. 1185-1191, 2004.
- S. Nassif-Khalil and C.A.T. Salama, "Super-Junction LDMOST on a Silicon-on-Sapphire Substrate", IEEE Trans. On Electron Devices, vol. 50, pp. 1385-1391, 2003.
- D. Suvakovic and C.A.T. Salama, "Energy Efficient Adiabatic Multiplier-Accumulator Design", Journal of VLSI Signal Processing, vol. 33, pp. 83-103, 2003.
- *N. Fujishima, A. Sugi, S. Kajiwara, K. Matsubara, Y. Nagayasu and C.A.T. Salama, "A High Density Low on Resistance Trench Lateral Power MOSFET with a Trench Bottom Source Contact", IEEE Trans. on Electron Devices, vol. 49, pp. 1462-1468, 2002.
- H. Djahanshahi, N. Saniei, S.P. Voinigescu, M.C. Maliepaard and C.A.T. Salama, "A 20GHz InP-HBT Voltage-Controlled Oscillator with Wide Frequency Tuning Range", IEEE Trans. On Microwave Theory and Techniques, vol. 49, pp. 1566-1572, 2001.
- W. Yang and C.A.T. Salama, "A 1.8V 15-bit 1mW 2nd-Order Sigma-Delta Modulator", J. on Analog IC and Signal Processing, vol. 26, pp. 191-204, 2000.
- J.Z. Ren and C.A.T. Salama, "1V SOI NMOSFET with Suppressed Floating Body Effects", Solid State Electronics, vol. 44, pp. 1931-1937, 2000.
- M. Ramezani and C.A.T. Salama, "A 0.8um BiCMOS Gate Driver for IGBT Power Switch", J. on Analog Integrated Circuits and Signal Processing, vol. 24, pp. 175-185, 2000.

* Most significant papers.

- *H. Djahanshahi and C.A.T. Salama, "Differential CMOS Circuits for 622MHz/933MHz Clock and Data Recovery Applications", IEEE J. Solid State Circuits, vol. 35, pp. 847-855, 2000.
- H. Djahanshahi, F. Hansen and C.A.T. Salama, "Gigabit-per-Second, ECL-Compatible I/O Interface in 0.35 μ m CMOS", IEEE J. Solid State Circuits, vol. 34, pp.1074-1083, 1999.
- *J. Ranaweera, W.T. Ng and C.A.T. Salama, "Simulation Fabrication and Characterization of a 3.3V Flash ZE²PROM Array Implemented in a 0.8 μ m CMOS Process", Solid State Electronics, vol. 43, pp. 263-273, 1999.
- D. Hiemstra, A. Kizeev, L. Hou and C.A.T. Salama, "Dose Rate and Total Dose Dependence of Low Frequency Noise Performance, I-V Curves and Sidegating for GaAs MESFETs", IEEE Trans. on Nuclear Science, vol. 45, pp. 2616-2623, 1998.
- *X.B. Chen, P.A. Mawby, K. Board, and C.A.T. Salama, "Theory of a Novel Voltage-Sustaining Layer for Power Devices", Microelectronics Journal, vol. 29, pp. 1005-1011, 1998.
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- M. Aliahmad and C.A.T. Salama, "A High Voltage Line Driver for Subscriber Loop Interfaces in a Low Voltage Submicron BiCMOS Technology", J. on Analog Integrated Circuits and Signal Processing, vol. 17, pp. 261-274, 1998.
- T. Sowlati, Y. Greshishchev and C.A.T. Salama, "Phase-Correcting Feedback System for Class E Power Amplifier" IEEE J. Solid State Circuits, vol. 32, pp. 544-550, 1997.
- *Y. Li, C.A.T. Salama, M. Seufert, P. Schvan and M. King, "Design and Characterization of Submicron BiCMOS Compatible HV NMOS and PMOS Devices, IEEE Trans. on Electron Devices, vol. 44, pp. 331-338, 1997.
- J. Ranaweera, I. Kalastirsky, E. Gulersen, W.T. Ng and C.A.T. Salama, "A Novel Programming Method for High Speed, Low Voltage Flash E²PROM Cells", Solid State Electronics, vol. 39, pp. 981-989, 1996.
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- *S.P. Voinigescu, P.B. Rabkin, C.A.T. Salama and P.A. Blakey, "2D Numerical Investigation of the Impact of Compositional Grading on the Performance of Submicrometer Si-SiGe MOSFETs", IEEE Trans. on Electron Devices, vol. 42, pp. 1039-1046, 1995.
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- S. Voinigescu, K. Iniewski, R. Lisak, C.A.T. Salama, J.P. Noel and D.C. Houghton, "New Technique for the Characterization of Si/SiGe Layers using Heterostructure MOS Capacitors", Solid State Electronics, vol. 37, pp.1491-1501, 1994.
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- Z.R. Tang, C.A.T. Salama, J.P. Noel, D. Houghton and M. Buchanan, "Characteristics of Mesa and LOCOS-Isolated Molecular Beam Epitaxy SiGe Diodes", Canadian J. Physics, vol. 70, pp. 969-974, 1993.
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- *C.P. Chong, C.A.T. Salama and K.C. Smith, "An Imager with Built-in Image-Velocity Computation Capability", IEEE Trans. on Circuits and Systems for Video Technology, vol. 2, pp. 306-312, 1992.
- *C.P. Chong, C.A.T. Salama and K.C. Smith, "A Novel Technique for Image-Velocity Computation", IEEE Trans. on Circuits and Systems for Video Technology, vol. 2, pp. 313-318, 1992.
- *S. Liang, L.Z. Hou, T. Gu and C.A.T. Salama, "Latch-up Modeling of BiCMOS Merged Bipolar-MOS Structures", Solid State Electronics, vol. 35, pp. 1461-1469, 1992.
- M. Mittal and C.A.T. Salama, "A GaAs 8x8 Cross-Point Switch for High Speed Digital Communications," J. High Speed Electronics, vol. 3, pp. 1-12, 1992.
- C.P. Chong, C.A.T. Salama and K.C. Smith, "Real-Time Edge Detection and Image Segmentation", Journal on Analog Integrated Circuits and Signal Processing, vol. 2, pp. 117-130, 1992.
- K. Iniewski and C.A.T. Salama, "Optimization of the CV Profiling Method Based on Inverse Modeling", J. Vac. Science and Technology, vol. 10, pp. 480-484, 1992.
- D.H.K. Hoe and C.A.T. Salama, "GaAs Pipelined Dynamic Logic", Integration, vol. 12, pp. 93-105, 1991.
- D.H.K. Hoe and C.A.T. Salama, "Dynamic GaAs Logic Circuits", J. High Speed Electronics, vol. 2, pp. 163-183, 1991.

- *J.H. Pasternak and C.A.T. Salama, "GaAs MESFET Differential Pass-Transistor Logic", IEEE J. Solid State Circuits, vol. 26, pp. 1309-1316, 1991.
- *J.H. Pasternak and C.A.T. Salama, "Design of Submicrometer CMOS Differential Pass-Transistor Logic Circuits", IEEE J. Solid State Circuits, vol. 26, pp. 1249-1258, 1991.
- *D.H.K. Hoe and C.A.T. Salama, "GaAs Trickle Transistor Domino Logic (TTDL)", IEEE J. Solid State Circuits, vol. 26, pp. 1441-1448, 1991.
- W.T. Ng and C.A.T. Salama, "A CMOS-Compatible Complementary SINFET HVIC Process", IEEE Trans. on Electron Devices, vol. 38, pp. 1935-1942, 1991.
- M. Patel, P. Ratnam and C.A.T. Salama, "A Novel Body Contact for SIMOX Based SOI MOSFETs", Solid State Electronics, vol. 34, pp. 1071-1075, 1991.
- D. Hoe and C.A.T. Salama, "Dynamic GaAs Capacitively Coupled Domino Logic (CCDL)", IEEE J. of Solid State Circuits, vol. 26, pp. 844-849, 1991.
- A. Nezar and C.A.T. Salama, "Breakdown Voltage in LDMOS Transistors Using Internal Field Rings", IEEE Trans. on Electron Devices, vol. 38, pp. 1676-1680, 1991.
- *K. Iniewski and C.A.T. Salama, "A New Approach to CV Profiling with Sub-Debye-Length Resolution", Solid State Electronics, vol. 34, pp. 309-314, 1991.
- W.T. Ng, S. Liang and C.A.T. Salama, "SINFET Device Modeling", Solid State Electronics, vol. 33, pp. 1569-1580, 1990.
- *D.G. Nairn and C.A.T. Salama, "Current Mode Algorithmic A/D Converters", IEEE J. Solid State Circuits, vol. 25, pp. 997-1004, 1990.
- H.W. Singor and C.A.T. Salama, "A High Performance CMOS Compatible 8-bit Current Scaling D/A Converter, IEE Proceedings, vol. 137, Part G, pp. 169-174, 1990.
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- *D. Nairn and C.A.T. Salama, "A Ratio Independent Algorithmic Analog to Digital Converter Combining Current Mode and Dynamic Techniques", IEEE Trans. on Circuits and Systems, vol. 37, pp. 319-325, 1990.
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- *Z. Parpia and C.A.T. Salama, "Optimization of RESURF LDMOS Transistors: An Analytical Approach", IEEE Trans. on Electron Devices, vol. 37, pp. 789-796, 1990.
- W. Ng, S. Liang and C.A.T. Salama, "Schottky Barrier Diode Characteristics Under High Level Injection", Solid State Electronics, vol. 33, pp. 39-46, 1990.
- K.J. Schultz, D.H.K. Hoe and C.A.T. Salama, "A Microprogrammable Processor Using Single Poly EPROM", Integration, vol. 8, pp. 189-199, 1989.
- J.K.O. Sin, C.A.T. Salama, and L.Z. Hou, "Transient Characteristics of N-Channel Hybrid Schottky Injection FET's", IEEE Trans. on Electron Devices, vol. 36, pp. 993-1000, 1989.
- J.K.O. Sin, C.A.T. Salama, V. Rumennik and S. Mukherjee, "High Voltage Characteristics of Resurfed Schottky Injection FET's", Solid State Electronics, vol. 34, pp. 317-326, 1989.

- S. Tarasewicz and C.A.T. Salama, "Threshold Voltage Characteristics of Ion Implanted Depletion MOSFETs", Solid State Electronics, vol. 33, pp. 1441-1446, 1988.
- *Z. Parpia, C.A.T. Salama and R. Hadaway, "A CMOS-Compatible High-Voltage IC Process", IEEE Trans. on Electron Devices, vol. 35, pp. 1687-1694, 1988.
- Z. Parpia, C.A.T. Salama and R. Hadaway, "Modelling and Characterization CMOS Compatible High Voltage Device Structures", IEEE Trans. on Electron Devices, vol. ED-34, pp. 2335-2343, 1987.
- S. Wong and C.A.T. Salama, "Improved Simulation of p and n channel MOSFETs Using an Enhanced SPICE MOS3 Model", IEEE Trans. on CAD, vol. CAD-6, pp. 586-590, 1987.
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- A.S. Shubat, J.A. Pretorius and C.A.T. Salama, "Expandable Arithmetic Block Macrocell", Integration, vol. 5, pp. 47-71, 1987.
- *J. Sin, C.A.T. Salama and L. Hou, "The SINFET - A Schottky Injection MOS-Gated Power Transistor", IEEE Trans. on Electron Devices, vol. 33, pp. 1940-1947, 1986.
- *Z. Parpia, J.G. Mena and C.A.T. Salama, "A Novel CMOS Compatible High-Voltage Transistor Structure", IEEE Trans. on Electron Devices, vol. 33, pp. 1948-1952, 1986.
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- S. Tarasewicz and C.A.T. Salama, "Simulation of the Accumulation-Punchthrough Mode in Depletion MOSFETs", Solid State Electronics, vol. 29, pp. 1025-1034, 1986.
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- *J.A. Pretorius, A.S. Shubat and C.A.T. Salama, "Latched Domino CMOS Logic", IEEE J. of Solid State Circuits, vol. SC-21, pp. 514-522, 1986.
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- J. Sin and C.A.T. Salama, "Wideband DMOS Amplifier Competes with Bipolar", Microwaves and RF, vol. 25, pp. 113-120, June 1986.
- J. Sin and C.A.T. Salama, "High Frequency Distortion Analysis in DMOS Transistors", Solid State Electronics, vol. 28, pp. 1223-1233, June 1985.
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- Z. Parpia, J. Mena and C.A.T. Salama, "A Novel CMOS Compatible High Voltage Transistor Structure," in High Voltage Integrated Circuits; J. Baliga, Editor; pp. 116-120, IEEE Press, N.Y., 1988.
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- N. Friedman, C.A.T. Salama, F.E. Holmes and P.M. Thompson, "Realization of a Multivalued Integrated Injection Logic (MP^2L) Full Adder," pp. 280-283, in "Integrated Injection Logic," J.E. Smith, Editor, IEEE Press, New York, 1980.

• PERSONNEL TRAINING**I. GRADUATE STUDENT THESES SUPERVISED:****CAREER TOTALS:**

- Ph.D. 33
- M.A.Sc.* 86
- M.Eng. 1

II. POST DOCTORAL FELLOWS/RESEARCH ASSOCIATES

CAREER TOTALS: 34

-
- Research oriented Thesis

• MAJOR CONTRIBUTIONS TO ENGINEERING

TECHNOLOGY AND PRACTICE

● Research

- Made fundamental and internationally recognized contributions in the area of semiconductor device research as well as in analog and digital microchip design for applications in telecommunications and computer systems. These contributions are documented in over 340 refereed publications and 16 patents.
- By recognizing the fundamental importance of interaction with industry, and in conjunction with his graduate students, ensured that his contributions to the design, development and implementation of novel microelectronic devices and integrated circuits were transferred to industry. These contributions have been and are presently in use in the microelectronic industry worldwide and have had a significant impact on:
 - Micropower device and circuit design
 - Power semiconductor device and high voltage integrated circuit design
 - Heterojunction bipolar and MOS transistors (SiGe) design, modeling, fabrication
 - CMOS current mode analog IC design
 - CMOS/BiCMOS high speed logic design
 - GaAs Dynamic logic design
- Presently involved in industrial cooperation in the area of microelectronics and information technology with several Canadian, US and Japanese corporations.

● Promotion and Management of Research Activity

- Scientific Director of, and a Principal Investigator in, Micronet: a Federal Network of Centres of Excellence focussing on research in microelectronic devices, circuits and systems. Micronet's budget is \$4.3M/year from federal government and industry sources. Micronet involves 20 universities working in close cooperation with 49 Canadian industrial corporations and has been in operation since 1990. Micronet received its third funding mandate for the period 1998-2005. The University of Toronto is the host of the Administrative Centre for the Network. Over the last 15 years, Micronet has contributed over \$50M to microelectronics research in Canada.
- Founding Chairman of the Board of Directors and a member of the Board of Directors of the Canadian Microelectronics Corporation (CMC). CMC was set up by NSERC in 1984 as a result of a proposal made by a university-industry committee chaired by A. Salama. CMC, during its first five years (1984-89) of operation was funded by a \$19.8M grant from NSERC. Funding for CMC was renewed for a further five years in 1989 (\$23.6M), in 1994 (\$22M over five years), and again in 2000 (\$30M over five years). CMC has had a significant impact on the development of a strong Canadian presence in the field of microchip design both at the university level and in industry. CMC at present involves 38 Canadian universities and 10 industrial corporations.
- Principal Investigator (1987-1997) and Microelectronics Area Coordinator (1987-90) for the Information Technology Research Centre, a Centre of Excellence funded by the Province of Ontario.
- Principal Investigator (1998-2001) for Communications and Information Technology Ontario (CITO), a centre of excellence funded by the Province of Ontario.
- Set up what is considered to be one of the major university microelectronic design and fabrication facility in Canada.

● Research Personnel Training

- Has trained 33 Ph.D's, 86 M.A.Sc's and 1 M.Eng. over the last thirty-seven years at the University of Toronto. Most of these researchers are now in senior managerial positions in industry or in professorial positions in Canada, the United States, Ireland, Japan, France, Hong Kong and China.

EXHIBIT A

ACKNOWLEDGMENT AND AGREEMENT TO BE BOUND

I, C. Andre T. Salama [print or type full name], of 66 Castlewood Road, Toronto, Ontario, Canada, M5N 2L2 [print or type full address], declare under penalty of perjury that I have read in its entirety and understand the Stipulated Protective Order (the "Order") that was issued by the United States District Court for the Northern District of California on August 2, 2007 [date] in the case of C 07-02664 JSW (the "Action"). I agree to comply with and to be bound by all the terms of this Order and I understand and acknowledge that failure to so comply could expose me to sanctions and punishment in the nature of contempt. I solemnly promise that I will not disclose in any manner any information or item that is subject to this Order to any person or entity except in strict compliance with the provisions of this Order.

I further agree to submit to the jurisdiction of the United States District Court for the Northern District of California for the purpose of enforcing the terms of this Order, even if such enforcement proceedings occur after termination of this Action.

Date: August 7, 2007

City and State where sworn and signed: Toronto, Ontario, Canada

Printed name: C. Andre T. Salama
[printed name]

Signature: 
[signature]

EXHIBIT 3

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and
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and
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Matthew R. Hulse
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October 30, 2007

VIA EMAIL

Harry F. Doscher
Morgan Lewis & Bockius LLP
2 Palo Alto Square
3000 El Camino Real, Suite 700
Palo Alto, CA 94306

Re: Alpha & Omega Semiconductor, Ltd. v. Fairchild Semiconductor Corp.
Case No. C 07-2638 JSW (consolidated with Case No. C 07-2664 JSW)
Our File No. 18865P-021600

Dear Harry:

I write in response to your letter dated October 23, 2007 concerning Dr. C. Andre T. Salama. In the letter, you state that AOS intends to disclose "Confidential" or "Highly Confidential -- Attorneys' Eyes Only" information to him. For the reasons set forth below, we object to the disclosure.

We cannot permit the requested disclosure because we are concerned about Dr. Salama's current consulting activities and lack sufficient information about them. Dr. Salama's relationship with Fuji Electric Co., Ltd., for example, is potentially problematic. AOS has not disclosed any information about his work for Fuji Electric. Based on our own investigation, however, we have learned that it involves power MOSFET technology.

We are also concerned about Dr. Salama's work on behalf of Micronet and the Canadian Microelectronics Corporation (CMC). He holds senior positions with these entities, which work with a large number of companies on microelectronics research. AOS has failed to disclose sufficient information about Dr. Salama's work with Micronet and CMC, including whether any of it involves power MOSFET technology. Additionally, due to AOS's failure to disclose Dr. Salama's work for Fuji Electric, we are also concerned about whether he is doing other relevant work which AOS has not disclosed to us.

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Harry F. Doscher
Page 2

If AOS provides additional information, we are willing to consider the issue further. But, based on the information we have received to date, we cannot permit Dr. Salama to review "Confidential" or "Highly Confidential -- Attorneys' Eyes Only" information.

Very truly yours,

/s/
Matthew R. Hulse

EXHIBIT 4

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Harry F. Doscher
Associate
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November 8, 2007

VIA Email and First Class Mail

Matthew R. Hulse, Esq.
Townsend and Townsend and Crew LLP
Two Embarcadero Center, 8th Floor
San Francisco, CA 94111
mrhulse@townsend.com

Re: *Alpha & Omega Semiconductor, Ltd. and Alpha & Omega Semiconductor, Inc. v. Fairchild Semiconductor Corporation,*
Nos. C 07-2638 JSW and C 07-2664 JSW (N.D. Cal.)

Dear Matthew,

I write in response to your October 30, 2007 letter objecting to the disclosure of confidential information to Dr. Andre Salama, in which you raise three specific objections.

First, despite your assertions, Dr. Salama has never had a consulting relationship with Fuji Electric Co., Ltd. Although three of the patents on which Dr. Salama is named as a co-inventor are assigned to Fuji, those patents are the result of work performed by graduate students to whom Dr. Salama was an academic advisor. If Fuji provided funding for those graduate students' research it did so either directly or through the University of Toronto, not through any agreement with Dr. Salama. The assignment of Dr. Salama's interest in these patents was the act and decision of his employer, the University of Toronto.

Second, both Micronet and the Canadian Microelectronics Corporation (CMC) are organized to support academic research. Micronet provides support in the form of research grants to universities; CMC provides support in the form of infrastructure. Neither entity conducts any product development or manufacturing. Neither entity gains an ownership interest in the intellectual property developed by supported research; such IP remains the property of the University at which it is developed. Dr. Salama does not have a technical consulting role at either organization, and in fact his role on the Board of Directors of CMC terminated in 1997.

Matthew R. Hulse, Esq.
November 8, 2007
Page 2


Morgan Lewis
COUNSELORS AT LAW

Dr. Salama's role in both organizations involved high level budgeting decisions-- he does not control individual grants at Micronet and did not have control of individual grants at CMC.

Third, your concern whether Dr. Salama is doing "other relevant work which AOS has not disclosed to us" is based on your misplaced assertion that Dr. Salama performed work for Fuji. As explained above, that assertion is incorrect.

AOS has fully complied with the requirements of the Protective Order by making a full and complete disclosure of Dr. Salama's relevant education and consulting and technical experience. Please confirm by close of business tomorrow that Fairchild is withdrawing all objections to disclosure of Fairchild's "Confidential" and "Highly Confidential -- Attorneys' Eyes Only" information to Dr. Salama. If we do not hear from you by close of business tomorrow we will prepare and file our motion with the Court.

Best Regards,



Harry F. Doscher

cc: Leonard J. Augustine, Jr., Esq. (w/Enclosures via email: ljaugustine@townsend.com)
Eric P. Jacobs, Esq. (w/Enclosures via email: epjacobs@townsend.com)
Igor Shoiket (w/Enclosures via email: ishoiket@townsend.com)
Priya Sreenivasan, Esq. (w/Enclosures via email: psreenivasan@townsend.com)
Brett M. Schuman, Esq. (w/Enclosures via email: bschuman@morganlewis.com)
Andrew J. Wu, Esq. (w/Enclosures via email: awu@morganlewis.com)

EXHIBIT 5

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November 9, 2007

VIA EMAIL

Harry F. Doscher
Morgan Lewis & Bockius LLP
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Palo Alto, CA 94306

Re: Alpha & Omega Semiconductor, Ltd. v. Fairchild Semiconductor Corp.
Case No. C 07-2638 JSW (consolidated with Case No. C 07-2664 JSW)
Our File No. 18865P-021600

Dear Harry:

I write in response to your letters dated November 8, 2007 concerning Cary Yang and Andre Salama.

Based on the information AOS has provided, we are withdrawing our objection to Dr. Yang. As for Dr. Salama, however, we maintain our objection and will not permit him to have access to Fairchild's "Confidential" and "Highly Confidential -- Attorneys' Eyes Only" information at this time.

We are concerned about the nature of Dr. Salama's relationship with Fuji Electric because we have received inadequate information about his work with the company. You state in the letter, for example, that Dr. Salama "never had a consulting relationship" with Fuji Electric and that his patents "are the result of work performed by graduate students," not by Dr. Salama. Through our own investigation, however, we have discovered that Dr. Salama has a far more significant relationship with Fuji Electric than AOS has disclosed to date. Indeed, Dr. Salama has been involved in developing intellectual property and technology in the power MOSFET field on behalf of Fuji Electric for a long time. Dr. Salama, together with Fuji Electric employees, are named as co-inventors on three patents and three patent applications relating to power MOSFET technology that are assigned to Fuji Electric. (See U.S. Patent Nos. 6,781,197, 6,800,904, and 7,005,352, and U.S. Patent App. Nos. 20040075138, 20040256666, and 20050142713.) To be properly named as a co-inventor, Dr. Salama must have necessarily collaborated with Fuji Electric employees in the conception of the claimed inventions.

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Harry F. Doscher
November 9, 2007
Page 2

Similarly, Dr. Salama is listed as a co-author with Fuji Electric employees on several technical articles concerning power MOSFET technology. (See N. Fujishima *et al.*, "A High Density Low on Resistance Trench Lateral Power MOSFET with a Trench Bottom Source Contact," IEEE Trans. on Electron Devices, vol. 49, pp. 1462-1468 (2002); A. Sugi *et al.*, "A 30V Class Extremely Low On-Resistance Meshed Trench Lateral Power MOSFET," ISPSD, Santa Fe, Proceedings, pp. 297-300 (2002); N. Fujishima and C.A.T. Salama, "A Trench Lateral Power MOSFET Using Self-Aligned Trench Bottom Contact Holes," IEDM, Washington, Proceedings, pp. 359-362 (1997).) Contrary to your assertions, these articles demonstrate that he plainly works with Fuji Electric in developing power MOSFET technology.

We remain willing to try to resolve this dispute without Court intervention. For Fairchild to consider this issue further, though, we request that AOS provide a full description of Dr. Salama's relationship with Fuji Electric, and explain why AOS believes his work in developing intellectual property and technology with Fuji Electric does not create a risk of competitive harm to Fairchild. We also request that AOS confirm that Dr. Salama is not currently doing any work (including without limitation research, intellectual property development, consulting, or product development) with any other company in the power MOSFET industry. If he is, please provide a description of the work.

Very truly yours,

/s/
Matthew R. Hulse

EXHIBIT 6

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November 14, 2007

VIA Email and First Class Mail

Matthew R. Hulse, Esq.
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Re: *Alpha & Omega Semiconductor, Ltd. and Alpha & Omega Semiconductor, Inc. v. Fairchild Semiconductor Corporation,*
Nos. C 07-2638 JSW and C 07-2664 JSW (N.D. Cal.)

Dear Matthew,

I write in response to your November 9, 2007 letter in which you reiterate Fairchild's objection to the disclosure of confidential information to Dr. Andre Salama.

As explained in my November 8, 2007 letter to you, Dr. Salama has never had a consulting relationship with Fuji Electric Co., Ltd. The fact that Dr. Salama is named as a co-inventor on three patents and three patent applications that have been assigned to Fuji does not conclusively establish that Dr. Salama provided professional services to Fuji, particularly in the context of the actual facts. Rather, as we have already explained, those patents and applications are the result of work performed by graduate students to whom Dr. Salama was an academic advisor in his role at the University of Toronto. Whether or not Dr. Salama's former graduate students ultimately became employees of Fuji is irrelevant to the question of whether Dr. Salama himself has ever had any professional relationship with Fuji; he has not.

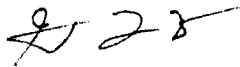
AOS has disclosed all of Dr. Salama's consulting and professional activities during the prior five years, in full satisfaction of the Protective Order. Fairchild has come forward with no conclusive evidence that Dr. Salama has performed any professional services on behalf of Fuji or any other undisclosed entity. In light of AOS's full disclosure and specific assurances regarding Fuji, Fairchild's continued objections to Dr. Salama are unfounded. Under the terms of the Stipulated Protective Order, it is our understanding that Fairchild bears the burden of seeking a Protective

Matthew R. Hulse, Esq.
November 14, 2007
Page 2

Morgan Lewis
C O U N S E L O R S A T L A W

Order if it objects to AOS's disclosure of confidential information to Dr. Salama. Accordingly, and for purposes of reaching a timely resolution of this dispute, please be advised that we intend to begin disclosing Fairchild's "Confidential" and/or "Highly Confidential – Attorneys' Eyes Only" information to Dr. Salama on November 21, 2007, unless Fairchild files a motion seeking to prohibit such disclosure.

Best Regards,



Harry F. Doscher

cc: Leonard J. Augustine, Jr., Esq. (w/Enclosures via email: ljaugustine@townsend.com)
Eric P. Jacobs, Esq. (w/Enclosures via email: epjacobs@townsend.com)
Igor Shoiket (w/Enclosures via email: ishoiket@townsend.com)
Priya Sreenivasan, Esq. (w/Enclosures via email: psreenivasan@townsend.com)
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EXHIBIT 7

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November 20, 2007

VIA EMAIL

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Re: Alpha & Omega Semiconductor, Ltd. v. Fairchild Semiconductor Corp.
Case No. C 07-2638 JSW (consolidated with Case No. C 07-2664 JSW)
Our File No. 18865P-021600

Dear Harry:

I write in response to your letter dated November 14, 2007 concerning Andre Salama. We continue to object to the disclosure of any Fairchild "Confidential" or "Highly Confidential -- Attorneys' Eyes Only" information to Dr. Salama. Simply put, AOS has failed to provide sufficient information about Dr. Salama's work with Fuji Electric for us to assess whether his access to confidential information is appropriate. AOS therefore cannot disclose Fairchild's confidential information to him. Any unauthorized disclosure is a violation of the Protective Order. If it occurs, we will seek all appropriate relief including sanctions against anyone who discloses the information to Dr. Salama.

The parties, however, may be able to resolve this dispute without court intervention if AOS provides sufficient information about Dr. Salama. We previously asked AOS to describe the nature of Dr. Salama's current relationship with Fuji Electric. In the letter dated November 14, 2007, however, you fail to provide the requested information. Instead, you assert that Dr. Salama never had a "consulting relationship" or "professional relationship" with Fuji Electric, but do not disclose whether he has any other type of relationship with the company. He plainly has had some type of relationship -- whether it be called "consulting," "professional," or something else -- as he is a named co-inventor or co-author with Fuji Electric personnel on several patents, patent applications, and technical articles.

We once again request that AOS disclose the nature of Dr. Salama's current relationship, if any, with Fuji Electric, including a description of the type of work he performs for them.

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Harry F. Doscher
November 20, 2007
Page 2

Additionally, please explain how Dr. Salama became a named co-inventor on Fuji Electric patents and patent applications, and a co-author of technical articles with Fuji Electric personnel, even though he allegedly has not had a "consulting" or "professional" relationship with the company.

We hope the parties can resolve this issue and avoid court intervention. We will file a motion by November 30, however, if we fail to resolve it.

Very truly yours,

/s/

Matthew R. Hulse